SENSITRON SEMICONDUCTOR

DATASHEET 5182, REV F.1

SURFACE MOUNT ULTRAFAST RECTIFIER (MELF)



DESCRIPTION: 1200 VOLT, 1.0 AMP, 40 NS RECTIFIER IN A SURFACE MOUNT (MELF) PACKAGE

MAXIMUM RATINGS

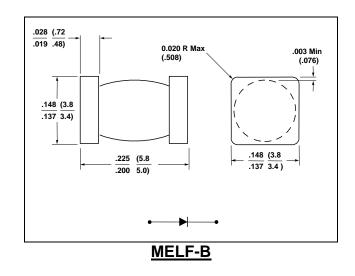
ALL RATINGS ARE	ALL RATINGS ARE AT TA=25°C UNLESS OTHERWISE SPECIFIED.							
RATING	SYMBOL	MIN	MAX	UNITS				
BREAKDOWN VOLTAGE	V _{BR}	1200		Volts				
PEAK INVERSE VOLTAGE	PIV		900	Volts				
MAXIMUM AVERAGE DC OUTPUT CURRENT	Ι _ο		1.0	Amps				
PEAK SINGLE CYCLE SURGE CURRENT	I _{FSM}		40	Amps				
(t _p =8.3 ms, half sine wave)								
MAXIMUM THERMAL RESISTANCE	$R_{ ext{ heta}JC}$		10	°C/W				
(Junction to end cap)								
THERMAL IMPEDANCE	Z _{θJX}		2.5	°C/W				
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	T _{op,sig}	-65	+175	°C				

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
FORWARD VOLTAGE DROP 300µs pulse	IF=0.1 A	V _F			1.05	Volts
	IF=0.2 A	V _F			1.20	Volts
FORWARD VOLTAGE DROP 300µs pulse	T _A = -55°C, IF=1.0 A	V _F			3.2	Volts
	T _J =+100°C, IF=0.1 A	V _F		0.68	0.75	Volts
REVERSE CURRENT @ 900V	T _A =25°C	I _R			2.0	μΑ
	T _A =100°C	I _R		20	30	μΑ
BREAKDOWN VOLTAGE	I _{BR} =50 μA	V _{BR}	1200			Volts
BREAKDOWN VOLTAGE	I _{BR} =50 μΑ, Τ _Α =-55°C	V _{BR}	1100			Volts
REVERSE RECOVERY TIME	I _F =500mA, I _R =1A,	t _{rr} @ 25°C		35	40	Nsec
	I _{RR} =250mA	t _{rr} @ 100°C		80	90	Nsec
JUNCTION CAPACITANCE	f=1MHz, V _R =10V, T _A =25°C	CJ		25	30	pF

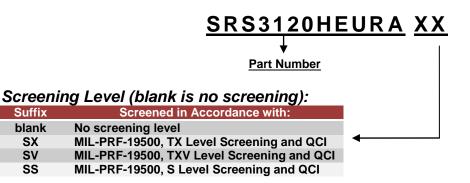
SENSITRON **TECHNICAL DATA** DATASHEET 5182, REV F.1

PACKAGE DIMENSIONS (inches/mm)



Note: The cathode side is marked with a dark colored band on one side of the diode body.

PART ORDERING INFORMATION



DISCLAIMER:

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SX

SV

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